

Si Zener-diode Chip – TK0S09ZDN

1. Scope

- The specification applies to planar Zener diode.
- Extra lower leakage current
- Special thickness for special assembly process.

2. Structure

- Planar type Zener diode.
- Electrode P (anode) : Aluminum. (Gold for option)
- Electrode N (cathode) side : Gold.

3. Size

- Chip size : 8.0mil × 8.0mil ± 0.8mil (0.2032mm × 0.2032mm ± 0.020mm)
- Thickness : 4.0mil / 6.0mil ± 0.6mil (0.110mm / 0.152mm ± 0.015mm)
- Pad Size : 6.0mil × 6.0mil ± 0.4mil (0.152mm × 0.152mm ± 0.010mm)
- Pattern drawing : per fig. 1

4. Electrical Characteristics

(Ta = +25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit.
Forward Voltage	V _F	Rank A: I _F = 10mA	3		5	V
		Rank B: I _F = 10mA	5		7	V
		Rank C: I _F = 10mA	6		8	V
		Rank H: I _F = 10mA	6		8	V
Forward Leakage current	I _F	Rank A: V _F = 2.5V			500	nA
		Rank B: V _F = 4V			500	nA
		Rank C: V _F = 5V			500	nA
		Rank H: V _F = 5V			500	nA
Reverse Voltage	V _Z	Rank A: I _R = 10mA	3.5		6	V
		Rank B: I _R = 10mA	8		13	V
		Rank C: I _R = 10mA	8		13	V
		Rank H: I _R = 10mA	20			V
Reverse Leakage current	I _R	Rank A: V _R = 3V			500	nA
		Rank B: V _R = 4V			500	nA
		Rank C: V _R = 5V			500	nA
		Rank H: V _R = 5V			500	nA

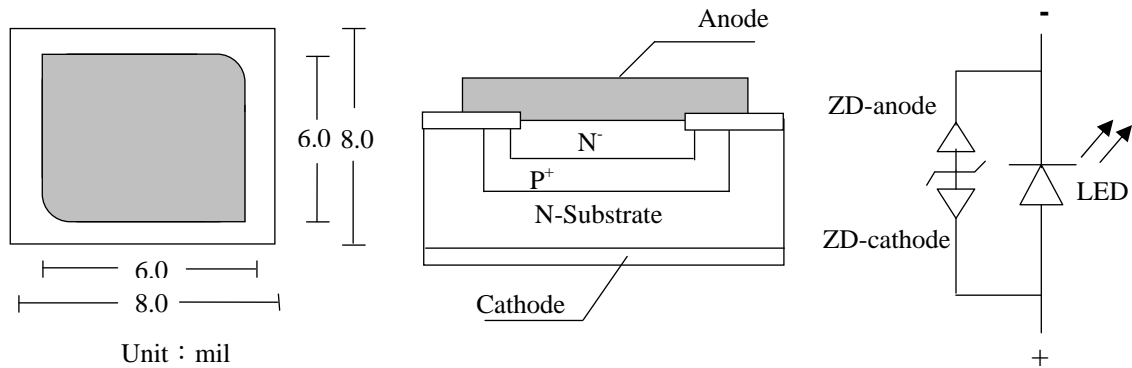


fig. 1

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